

**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
-30V	65mΩ @ V <sub>GS</sub> = -10V	-3.8A
	99mΩ @ V <sub>GS</sub> = -4.5V	-3.0A

**Description**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

**Applications**

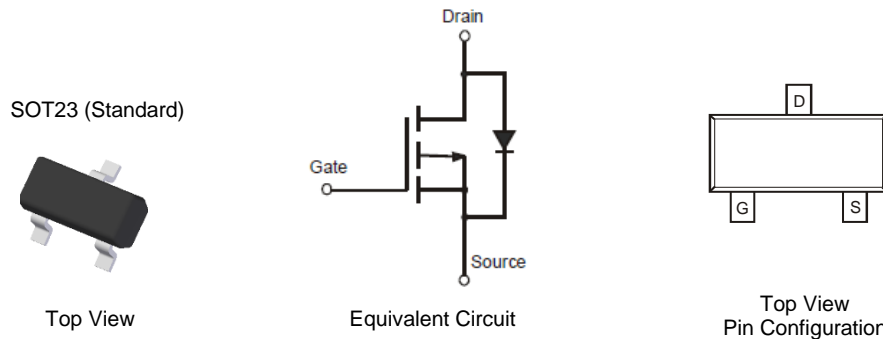
- Backlighting
- Power-management functions
- DC-DC converters

**Features and Benefits**

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An automotive-compliant part is available under a separate datasheet ([DMP3099LQ](#))**

**Mechanical Data**

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 **e3**
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

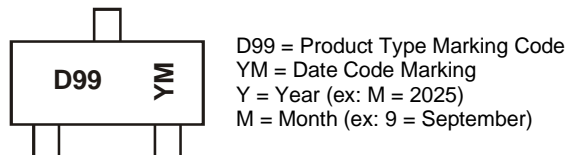


**Ordering Information** (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMP3099L-7	SOT23 (Standard)	3000	Tape & Reel
DMP3099L-13	SOT23 (Standard)	10000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**



Date Code Key

Year	2013	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	A	-	M	N	P	R	S	T	U	V	W	X

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	V
Drain Current (Note 5) $V_{GS} = -10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	-3.8	A
		$T_A = +70^\circ\text{C}$		-2.9	
Pulsed Drain Current (Note 6)			$I_{DM}$	-11	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_D$	1.08	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	115	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-30	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	-800	nA	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	—	-2.1	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	65	m $\Omega$	$V_{GS} = -10\text{V}, I_D = -3.8\text{A}$
				99		$V_{GS} = -4.5\text{V}, I_D = -3.0\text{A}$
Forward Transfer Admittance	$ Y_{fs} $	—	3.6	—	S	$V_{DS} = -5\text{V}, I_D = -2.7\text{A}$
Diode Forward Voltage (Note 6)	$V_{SD}$	—	—	-1.26	V	$V_{GS} = 0\text{V}, I_S = -2.7\text{A}$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	563	—	pF	$V_{DS} = -25\text{V}, V_{GS} = 0\text{V},$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	48	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	41	—	pF	
Gate Resistance	$R_G$	—	10.3	—	$\Omega$	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$
<b>SWITCHING CHARACTERISTICS (Note 8)</b>						
Total Gate Charge	$Q_g$	—	5.2	—	nC	$V_{DS} = -15\text{V}, V_{GS} = -4.5\text{V},$ $I_D = -3.8\text{A}$
			11			
Gate-Source Charge	$Q_{gs}$	—	1.7	—		
Gate-Drain Charge	$Q_{gd}$	—	1.9	—		
Turn-On Delay Time	$t_{d(on)}$	—	4.8	—	ns	$V_{DS} = -15\text{V}, V_{GS} = -10\text{V},$ $I_D = -1\text{A}, R_G = 6.0\Omega$
Rise Time	$t_r$	—	5.0	—		
Turn-Off Delay Time	$t_{d(off)}$	—	31	—		
Fall Time	$t_f$	—	15	—		

- Notes:
- Device mounted on FR-4 PCB on 2 oz., 0.5 inch<sup>2</sup> copper pads and  $t \leq 5$  sec.
  - Pulse width  $\leq 10\mu\text{s}$ , Duty Cycle  $\leq 1\%$ .
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

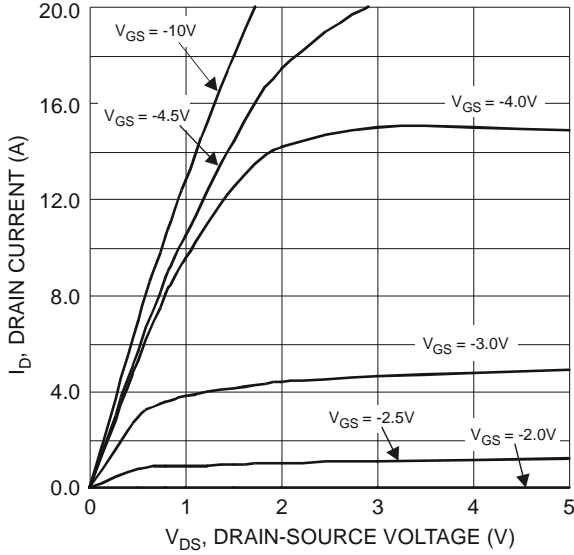


Figure 1 Typical Output Characteristics

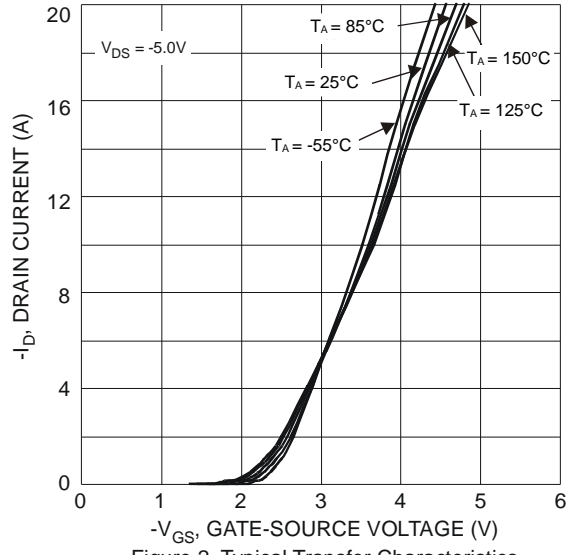


Figure 2 Typical Transfer Characteristics

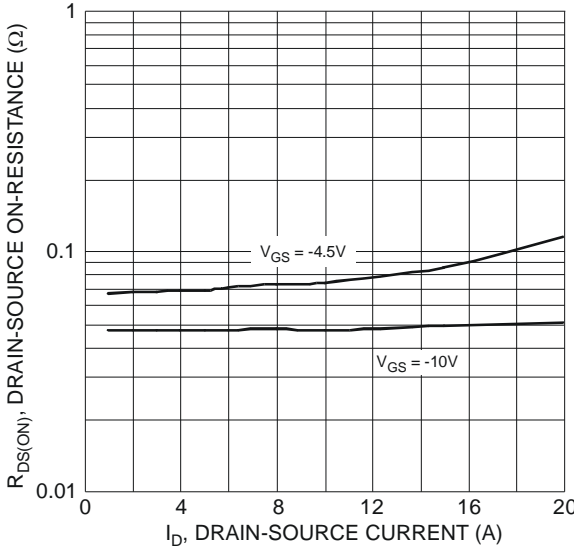


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

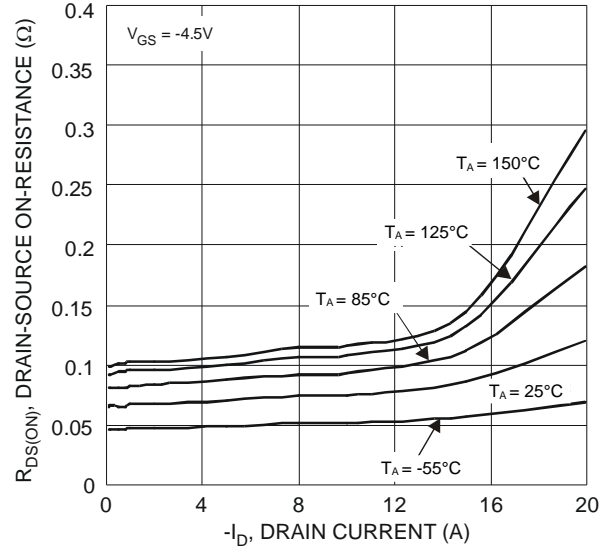


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

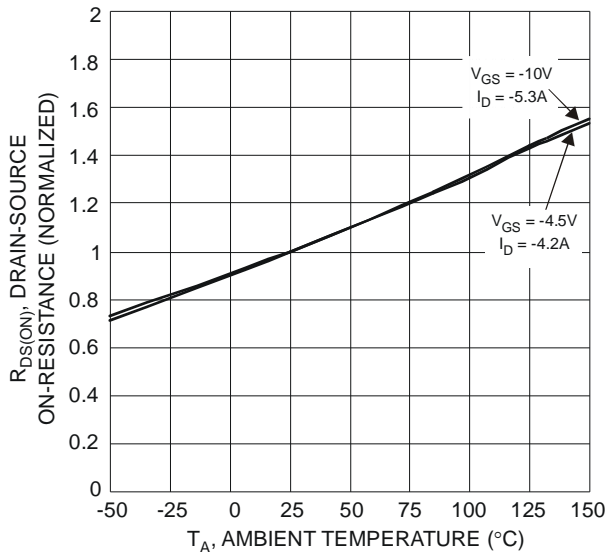


Figure 5 On-Resistance Variation with Temperature

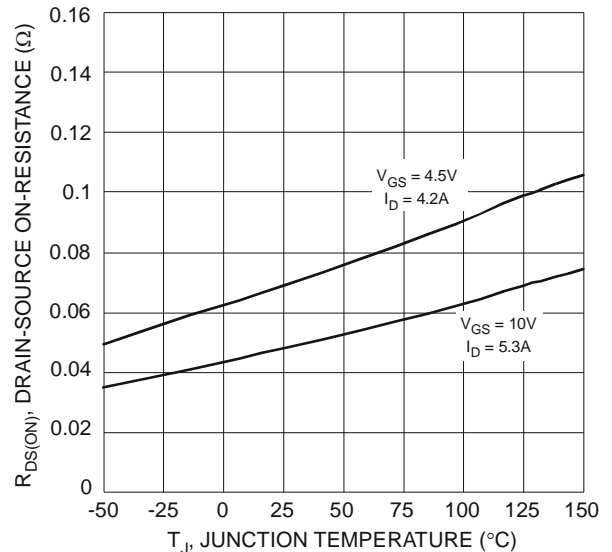


Figure 6 On-Resistance Variation with Temperature

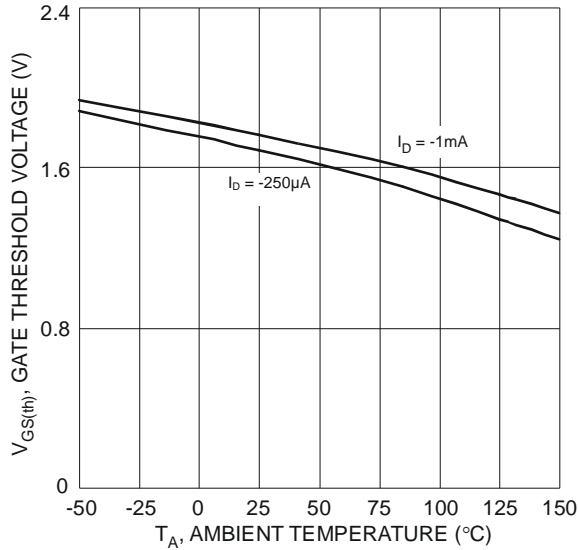


Figure 7 Gate Threshold Variation vs. Ambient Temperature

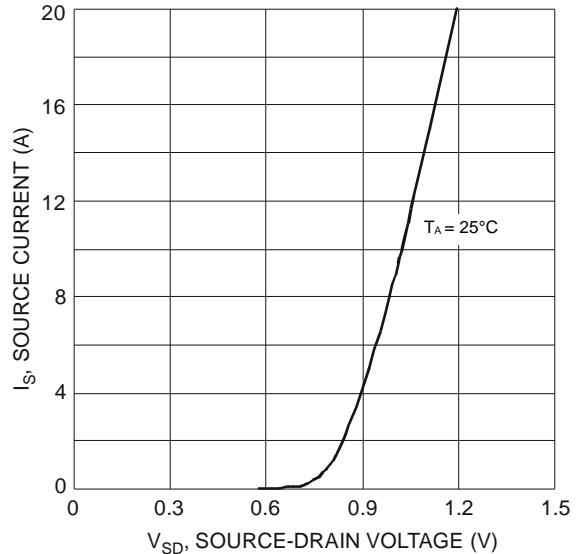


Figure 8 Diode Forward Voltage vs. Current

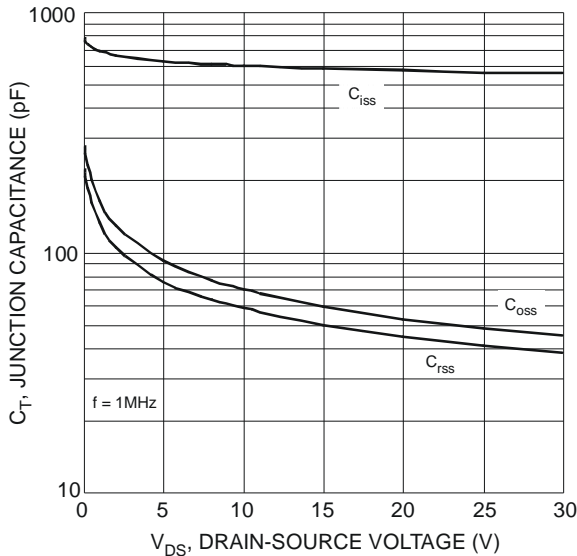


Figure 9 Typical Junction Capacitance

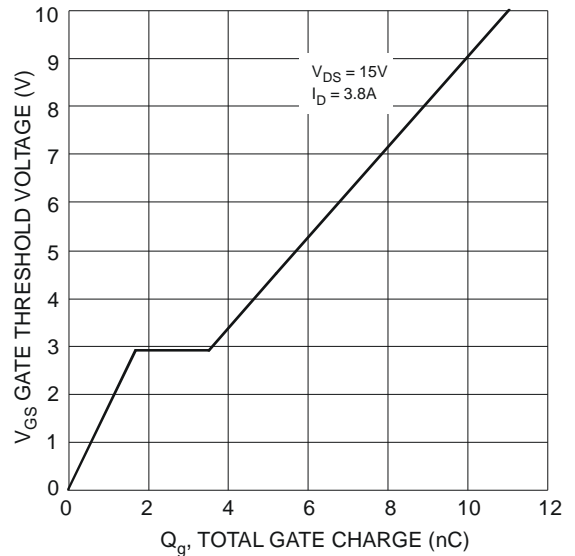


Figure 10 Gate Charge

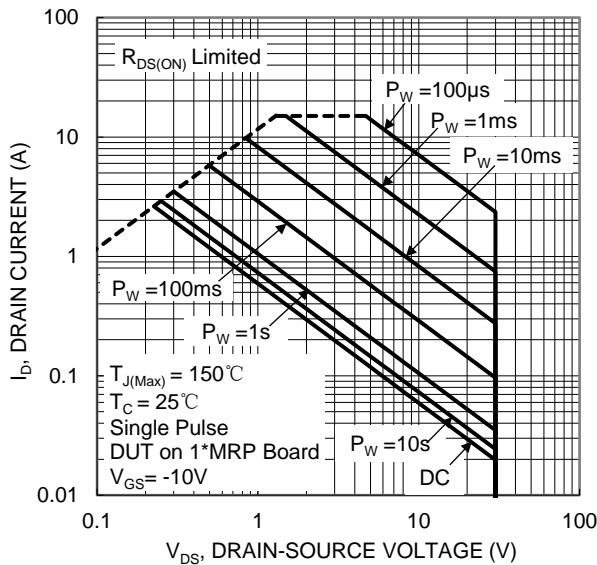
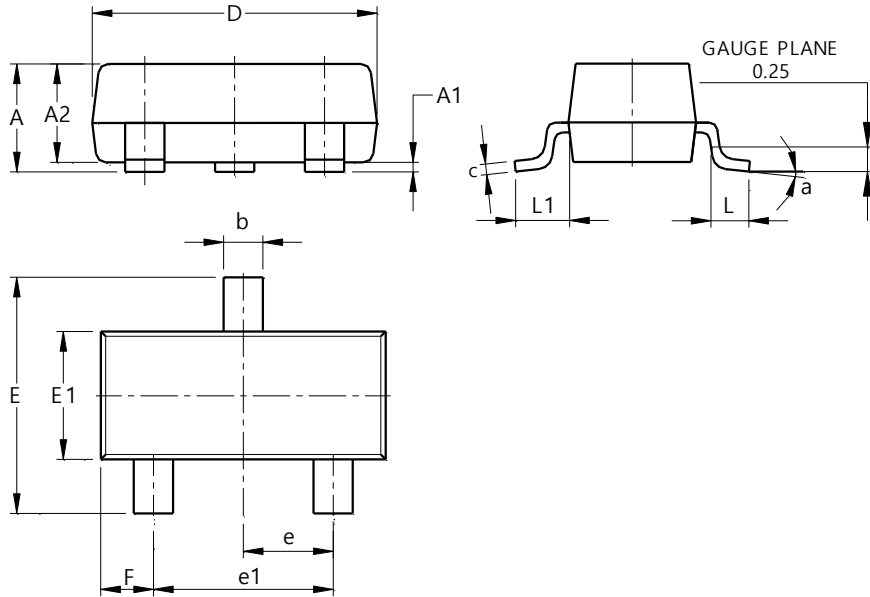


Figure 11. SOA, Safe Operation Area

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23 (Standard)**

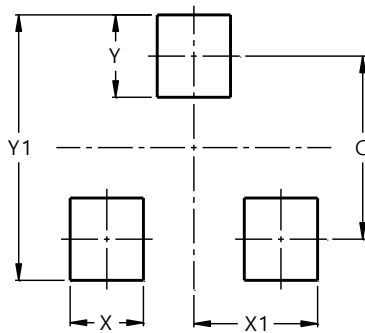


SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23 (Standard)**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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